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APR 25 2003 Docket No.: M4065.0814/P814
(PATENT)

TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Vladimir Berezin, et al

10/A
BA5-1403

Application No.: 09/653,527

Group Art Unit: 2816

Filed: August 31, 2000

Examiner: Not Yet Assigned

For: CMOS APS PIXEL SENSOR DYNAMIC
RANGE INCREASE

FIRST PRELIMINARY AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

Prior to examination on the merits, please amend the above-identified U.S. patent application as follows:

In the Specification

Please rewrite the paragraph beginning on page 6, lines 5-11 as follows:

After signal sampling is completed, the voltage on VDD line N-1 drops to 0 at 224 during the reset time for photodiode 223 for line N-1. This means that the floating diffusion for that photodiode 223 will be charged to the reset level when the output column is grounded and the surface potential under the source follower gate is minimum. This may increase the cell capacitance.

A1